NSN 5961-01-272-8945

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View Online at https://aerobasegroup.com/nsn/5961-01-272-8945

Inclosure Material:

Metal

Overall Length:

Between 0.890 inches and 0.910 inches

Overall Height:

Between 0.140 inches and 0.200 inches

Overall Width:

Between 0.375 inches and 0.395 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Emitter

Mounting Method:

Unthreaded hole

Features Provided:

High frequency and gold plated leads

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

30.0 breakdown voltage, collector-to-emitter, base open and 65.0 breakdown voltage, collector-to-base, emitter open and 4.0 breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

3.00 amperes source cutoff current

Power Rating Per Characteristic:

44.0 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Precious Material And Location:

Plated leads. Gold

Precious Material:

Gold

Test Data Document:

53711-5538013 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

3 ribbon and 1 case

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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